



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Atty. Docket

MARK SIMPSON ET AL

US 010610

Serial No. 10/015,847

Group Art Unit: 2822

Filed: DECEMBER 10, 2001

Examiner: M. LEWIS

Title: DUAL GATE OXIDE HIGH-VOLTAGE SEMICONDUCTOR DEVICE AND
METHOD FOR FORMING THE SAME

Commissioner for Patents
Washington, D.C. 20231

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Election
#6/A
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AMENDMENT

Sir:

In response to the official Office Action dated
October 21, 2002, please amend the above-identified application
as follows:

IN THE CLAIMS

Kindly cancel Claims 13-20 without prejudice.

REMARKS

In the outstanding Official Action, restriction was
required as between Claims 1-12, drawn to a dual gate oxide
high voltage semiconductor and Claims 13-20, drawn to a method
for forming a dual gate oxide high voltage semiconductor.

In response, Applicants hereby elect Claims 1-12 for
an examination on the merits, without prejudice to Applicants'